

INFRARED LEADS

FEATURES:

- High Radiant Intensity
- Emission angle suitable for remote control
- Colorless plastic molded lens
- Compatible with PIN Silicon Photo Diodes HPD711/712/726

USES:

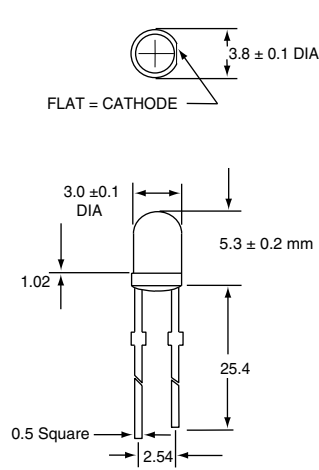
- Remote Control for Photo Sensor
- Optical Switch

Maximum Ratings (T_a=25°)

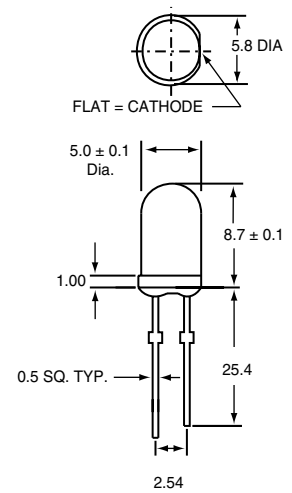
Forward Current (I_{FM}) = 100mA
 Pulse Forward Current (I_{FPM}) = 1A (1)
 Reverse Voltage (V_R) = 5V
 Power Dissipation (P_M) = 150mW
 Operating Temperature Range (T_{OP}) = -20 to +85°C
 Storage Temperature (T_{ST}) = -40 to + 100°C
 Soldering Temperature (T_{SOL})= 260°C (2)

(1): f=1KHz, t_p/T≤1%

(2): t_p/T≤3s, up to 4mm from the body of the device.



HIR303C/B



HIR305C/B

Optoelectric Characteristics (T_a=25°C)

PARAMETER	Unit	Test Condition	HIR303C/B.			HIR305C/B		
			Min.	Typ.	Max.	Min.	Typ.	Max.
Forward Voltage (V _F)	V	I _F = 50mA	-	1.3	1.5	-	1.3	1.5
Pulse Forward Voltage (V _{FP})	V	I _{FP} =1A t _p = 10μS	-	-	5	-	-	5
Reverse Current (I _R)	μA	V _R = 5V	-	-	50	-	-	50
Light Output Power (P _o)	mW	I _F =50mA	-	7.5	-	-	7.5	-
Radiant Intensity (I _E)	mW/sr	I _F =50mA	-	-	18	-	-	18
Peak Emission Wavelength (λ _P)	nm	I _F =50mA	-	945	-	-	945	-
Spectral Line Half Width (Δ/λ)	nm	I _F =50mA	-	45	-	-	45	-
Emission Angle of Half Intensity (Θ/2)	o	I _F =50mA	-	20	-	-	30	-
Junction Capacitance (C _i)	pF	V _R =1 f=1MHz	-	50	-	-	50	-
Switch Time (T _r / T _f)	μs	I _{FP} =100mA	-	1	-	-	1	-
		f=1KHz t _p /T= 1%	-	1	-	-	1	-